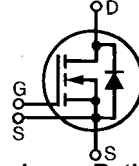


# HiPerFET™ Power MOSFETs

IXFN 200 N06  
IXFN 200 N07

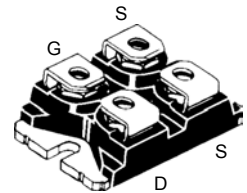
N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low  $t_{rr}$



| $V_{DSS}$ | $I_{D25}$ | $R_{DS(on)}$ |
|-----------|-----------|--------------|
| 60 V      | 200 A     | 6 mΩ         |
| 70 V      | 200 A     | 6 mΩ         |

$t_{rr} \leq 250$  ns

miniBLOC, SOT-227 B (IXFN)  
E153432



G = Gate  
S = Source  
D = Drain  
Either Source terminal at miniBLOC can be used as Main or Kelvin Source

| Symbol       | Test Conditions                                                                                                                             | Maximum Ratings |                  |                        |
|--------------|---------------------------------------------------------------------------------------------------------------------------------------------|-----------------|------------------|------------------------|
| $V_{DSS}$    | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$                                                                                             | N07             | 70               | V                      |
| $V_{DGR}$    | $T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1$ MΩ                                                                           | N06             | 60               | V                      |
| $V_{GS}$     | Continuous                                                                                                                                  |                 | ±20              | V                      |
| $V_{GSM}$    | Transient                                                                                                                                   |                 | ±30              | V                      |
| $I_{D25}$    | $T_C = 25^\circ\text{C}$ ; Chip capability                                                                                                  | 200N06          | 200              | A                      |
| $I_{L(RMS)}$ | Terminal current limit                                                                                                                      |                 | 100              | A                      |
| $I_{DM}$     | $T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$                                                                                  |                 | 600              | A                      |
| $I_{AR}$     | $T_C = 25^\circ\text{C}$                                                                                                                    |                 | 100              | A                      |
| $E_{AR}$     | $T_C = 25^\circ\text{C}$                                                                                                                    |                 | 30               | mJ                     |
| $E_{AS}$     | $T_C = 25^\circ\text{C}$                                                                                                                    |                 | 2                | J                      |
| dv/dt        | $I_S \leq I_{DM}$ , $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$ ,<br>$T_J \leq 150^\circ\text{C}$ , $R_{\theta JA} \leq 2^\circ\text{C/W}$ |                 | 5                | V/ns                   |
| $P_D$        | $T_C = 25^\circ\text{C}$                                                                                                                    |                 | 520              | W                      |
| $T_J$        |                                                                                                                                             |                 | -55 ... +150     | °C                     |
| $T_{JM}$     |                                                                                                                                             |                 | 150              | °C                     |
| $T_{stg}$    |                                                                                                                                             |                 | -55 ... +150     | °C                     |
| $V_{ISOL}$   | 10/50 Hz, RMS<br>$I_{ISOL} \leq 1$ mA                                                                                                       |                 | 2500<br>3000     | V~<br>V~               |
| $M_d$        | Mounting torque<br>Terminal connection torque                                                                                               |                 | 1.5/13<br>1.5/13 | Nm/lb.in.<br>Nm/lb.in. |
| Weight       |                                                                                                                                             |                 | 30               | g                      |

| Symbol       | Test Conditions                                                                                    | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |          |              |
|--------------|----------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|----------|--------------|
|              |                                                                                                    | min.                                                                              | typ.     | max.         |
| $V_{DSS}$    | $V_{GS} = 0$ V, $I_D = 1$ mA                                                                       | N06<br>N07                                                                        | 60<br>70 | V<br>V       |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 8$ mA                                                                   |                                                                                   | 2        | 4 V          |
| $I_{GSS}$    | $V_{GS} = \pm 20$ V <sub>DC</sub> , $V_{DS} = 0$                                                   |                                                                                   |          | ±200 nA      |
| $I_{DSS}$    | $V_{DS} = 0.8 \cdot V_{DSS}$ , $V_{GS} = 0$ V<br>$T_J = 125^\circ\text{C}$                         |                                                                                   | 2        | 400 μA<br>mA |
| $R_{DS(on)}$ | $V_{GS} = 10$ V, $I_D = 0.5 \cdot I_{D25}$<br>Pulse test, $t \leq 300$ μs, duty cycle $d \leq 2\%$ |                                                                                   |          | 6 mΩ         |

## Features

- International standard packages
- miniBLOC with Aluminium nitride isolation
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

## Applications

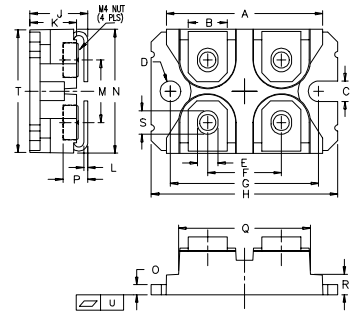
- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

## Advantages

- Easy to mount
- Space savings
- High power density

| Symbol       | Test Conditions                                                                                              | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |      |
|--------------|--------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|------|
|              |                                                                                                              | min.                                                                              | typ. | max. |
| $g_{fs}$     | $V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test                                                 | 60                                                                                | 80   | S    |
| $C_{iss}$    | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$                                                |                                                                                   | 9000 | pF   |
| $C_{oss}$    |                                                                                                              |                                                                                   | 4000 | pF   |
| $C_{rss}$    |                                                                                                              |                                                                                   | 2400 | pF   |
| $t_{d(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\ \Omega$ (External), |                                                                                   | 30   | ns   |
| $t_r$        |                                                                                                              |                                                                                   | 60   | ns   |
| $t_{d(off)}$ |                                                                                                              |                                                                                   | 100  | ns   |
| $t_f$        |                                                                                                              |                                                                                   | 60   | ns   |
| $Q_{g(on)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$                                  |                                                                                   | 480  | nC   |
| $Q_{gs}$     |                                                                                                              |                                                                                   | 60   | nC   |
| $Q_{gd}$     |                                                                                                              |                                                                                   | 240  | nC   |
| $R_{thJC}$   | miniBLOC, SOT-227 B                                                                                          | 0.05                                                                              | 0.24 | K/W  |
| $R_{thCK}$   | miniBLOC, SOT-227 B                                                                                          |                                                                                   |      | K/W  |

| Source-Drain Diode |                                                                                                                | Characteristic Values<br>( $T_J = 25^\circ\text{C}$ , unless otherwise specified) |      |               |
|--------------------|----------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|---------------|
| Symbol             | Test Conditions                                                                                                | min.                                                                              | typ. | max.          |
| $I_S$              | $V_{GS} = 0\text{ V}$                                                                                          |                                                                                   |      | 200 A         |
| $I_{SM}$           | Repetitive; pulse width limited by $T_{JM}$                                                                    |                                                                                   |      | 600 A         |
| $V_{SD}$           | $I_F = 100\text{ A}, V_{GS} = 0\text{ V}$ ,<br>Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$ |                                                                                   |      | 1.7 V         |
| $t_{rr}$           | $I_F = 25\text{ A}$<br>$-di/dt = 100\text{ A}/\mu\text{s}$ ,<br>$V_R = 50\text{ V}$                            |                                                                                   | 150  | 250 ns        |
| $Q_{RM}$           |                                                                                                                |                                                                                   | 0.7  | $\mu\text{C}$ |
| $I_{RM}$           |                                                                                                                |                                                                                   | 9    | A             |

**miniBLOC, SOT-227 B**

**M4 screws (4x) supplied**

| Dim. | Millimeter |       | Inches |       |
|------|------------|-------|--------|-------|
|      | Min.       | Max.  | Min.   | Max.  |
| A    | 31.50      | 31.88 | 1.240  | 1.255 |
| B    | 7.80       | 8.20  | 0.307  | 0.323 |
| C    | 4.09       | 4.29  | 0.161  | 0.169 |
| D    | 4.09       | 4.29  | 0.161  | 0.169 |
| E    | 4.09       | 4.29  | 0.161  | 0.169 |
| F    | 14.91      | 15.11 | 0.587  | 0.595 |
| G    | 30.12      | 30.30 | 1.186  | 1.193 |
| H    | 38.00      | 38.23 | 1.496  | 1.505 |
| J    | 11.68      | 12.22 | 0.460  | 0.481 |
| K    | 8.92       | 9.60  | 0.351  | 0.378 |
| L    | 0.76       | 0.84  | 0.030  | 0.033 |
| M    | 12.60      | 12.85 | 0.496  | 0.506 |
| N    | 25.15      | 25.42 | 0.990  | 1.001 |
| O    | 1.98       | 2.13  | 0.078  | 0.084 |
| P    | 4.95       | 5.97  | 0.195  | 0.235 |
| Q    | 26.54      | 26.90 | 1.045  | 1.059 |
| R    | 3.94       | 4.42  | 0.155  | 0.174 |
| S    | 4.72       | 4.85  | 0.186  | 0.191 |
| T    | 24.59      | 25.07 | 0.968  | 0.987 |
| U    | -0.05      | 0.1   | -0.002 | 0.004 |

IXYS reserves the right to change limits, test conditions, and dimensions.

|                                                                                  |           |           |           |           |           |           |             |
|----------------------------------------------------------------------------------|-----------|-----------|-----------|-----------|-----------|-----------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,881,106 | 5,017,508 | 5,049,961 | 5,187,117 | 5,486,715 | 6,306,728B1 |
|                                                                                  | 4,850,072 | 4,931,844 | 5,034,796 | 5,063,307 | 5,237,481 | 5,381,025 |             |



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